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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	. ATTORNEY DOCKET NO.	CONFIRMATION NO
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759	90 06/04/2003			
Patent Administrator Testa, Hurwitz & Thibeault, LLP High Street Tower 125 High Street			EXAMINER .	
			SCHILLINGER	, LAURA M
Boston, MA 02110			ART UNIT	PAPER NUMBER
•			2813	1.4
			DATE MAILED: 06/04/2003	14

Please find below and/or attached an Office communication concerning this application or proceeding.

c C	Application No.	Applicant(s)			
	10/022,689	FITZGERALD, EUGENE A.			
Office Action Summary	Examiner	Art Unit			
	Laura M Schillinger	2813			
The MAILING DATE of this communicat Period for Reply	ion appears on the cover sheet with	the correspondence address			
A SHORTENED STATUTORY PERIOD FOR THE MAILING DATE OF THIS COMMUNICA - Extensions of time may be available under the provisions of 37 after SIX (6) MONTHS from the mailing date of this communic - If the period for reply specified above is less than thirty (30) da - If NO period for reply is specified above, the maximum statuto - Failure to reply within the set or extended period for reply will, - Any reply received by the Office later than three months after the earned patent term adjustment. See 37 CFR 1.704(b).	TION. 7 CFR 1.136(a). In no event, however, may a repation. 195, a reply within the statutory minimum of thirty (ry period will apply and will expire SIX (6) MONTH by statute, cause the application to become ABA!	ly be timely filed 30) days will be considered timely. 4S from the mailing date of this communication. NDONED (35 U.S.C. § 133).			
Status 1) Paganansiya ta communication(s) filed	on 12 May 2002				
1) Responsive to communication(s) filed2a) This action is FINAL.2b)	on <u>73 Way 2003</u> ☐ This action is non-final.				
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 Since this application is in condition for closed in accordance with the practice Disposition of Claims 					
4)⊠ Claim(s) <u>35,39-41,44 and 45</u> is/are per	nding in the application.				
4a) Of the above claim(s) is/are withdrawn from consideration.					
5) Claim(s) is/are allowed.					
6) Claim(s) <u>35, 39-41, 44</u> is/are rejected.					
7)⊠ Claim(s) <u>45</u> is/are objected to.					
8) Claim(s) are subject to restriction	n and/or election requirement.				
Application Papers					
9) The specification is objected to by the E					
10) The drawing(s) filed on is/are: a)[
Applicant may not request that any objecti					
11) The proposed drawing correction filed on If approved, corrected drawings are required.		sapproved by the Examiner.			
12) The oath or declaration is objected to by					
Pri rity under 35 U.S.C. §§ 119 and 120	the Examinor.				
13) Acknowledgment is made of a claim for	foreign priority under 35 U.S.C. &	119(a)-(d) or (f)			
a) ☐ All b) ☐ Some * c) ☐ None of:	toroign priority and or or or or or				
1. ☐ Certified copies of the priority do	cuments have been received.				
2. Certified copies of the priority do		plication No.			
3. Copies of the certified copies of t	he priority documents have been ronal Bureau (PCT Rule 17.2(a)).	eceived in this National Stage			
14) Acknowledgment is made of a claim for o	· / / · / ·				
a) The translation of the foreign langu					
a) ☐ The translation of the foreign langu					
Attachment(s)					
 Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-3) Information Disclosure Statement(s) (PTO-1449) Pape 	-948) 5) Notice of In	ummary (PTO-413) Paper No(s) formal Patent Application (PTO-152)			



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DETAILED ACTION

This Office Action is in response to Amendment C, in Paper No.13, dated 5/13/03.

Allowable Subject Matter

Claim 45 is objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Ismail teaches forming a graded SiGe layer (30) under compressive strain and then later teaches to form a relaxed layer 40 upon it. Ismail teaches that this results in a strain at the interface of the two layers resulting in a valence jump (Col.6, lines: 40-50), therefore there is a reduction of relaxation. However, Ismail fails to teach the combination of claimed limitations required by claim 45, where the **graded compressed SiGe** layer experiences a reduction in **compressive strain** as a result of a **second tensile strained layer**. Other related prior art teaches a reduction in compressive strain for **AlGaN layers** as a result of a second tensile strained layer, however prior art fails to teach nor suggest this reduction for SiGe layers. Consequently, claim 45 contains allowable subject matter.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -



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(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 38-40 are rejected under 35 U.S.C. 102(b) as being anticipated by Ismail et al ('713).

In reference to claim 35, Ismail et al a method comprising:

Providing a semiconductor substrate (Fig.2 (20)); and

Providing on the substrate a graded region incorporating a first strain (Fig.2 (30) and Col.6. lines: 35-40); and

Processing the graded region so as to introduce a second type of strain, the previously incorporated first type strain reducing the processed induced second type of strain(Col.6, lines: 20-30-layer 40).

In reference to claim 39, Ismail teaches wherein the graded region comprises Si and Ge graded to an increasing concentration of Ge (Col.6. lines: 35-40), and the step of incorporating compressive strain comprises decreasing a temperature at which the graded region is grown as the Ge concentration increases in the graded region (Col.6, lines: 40-55).

In reference to claim 40, Ismail teaches wherein incorporating compressive strain comprises growing alloys of GeSi at 35-100%(Col.6, lines: 25-35).

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In reference to claim 41, Ismail teaches planarizing at least one surface (Col.4, lines: 45-50).

In reference to claim 44, Ismail teaches planarizing at least one surface (Col.4, lines: 45-50).

Response to Arguments

Applicant's arguments filed 5/20/03 have been fully considered but they are not persuasive. Applicant argues that Ismail fails to teach a first and second strain wherein processing results in the reduction of the second strain type. However as taught by Ismail the second strain type may be considered "relaxed" and the formation of layer 40 above layer 30 results in a increased strain and therefore a reduced relaxation and therefore anticipates the claim language of amended claim 1.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Laura M Schillinger whose telephone number is (703) 308-6425. The examiner can normally be reached on M-T, R-F 7:00-5:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl W Whitehead, Jr. can be reached on (703) 308-4940. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 308-7722 for regular communications and (703) 308-7722 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

CARL WHITEHEAD/JR.

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LMS May 30, 2003